

Product data sheet

### 1. General description

NPN low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

PNP complement: PBSS5160QA.

### 2. Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- High energy efficiency due to less heat generation
- Reduced Printed-Circuit Board (PCB) area requirements
- Solderable side pads
- AEC-Q101 qualified

### 3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	60	V
I <sub>C</sub>	collector current			-	-	1	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	1.5	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$\begin{split} I_C = 1 \text{ A}; \ I_B = 0.1 \text{ A}; \ \text{pulsed}; \ t_p \leq 300 \ \mu\text{s}; \\ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^\circ\text{C} \end{split}$		-	170	235	mΩ

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### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		С
2	Е	emitter		в
3	С	collector	4 3	- <b>h</b> a
4	С	collector	2 Transparent top view	E sym123
			DFN1010D-3 (SOT1215)	

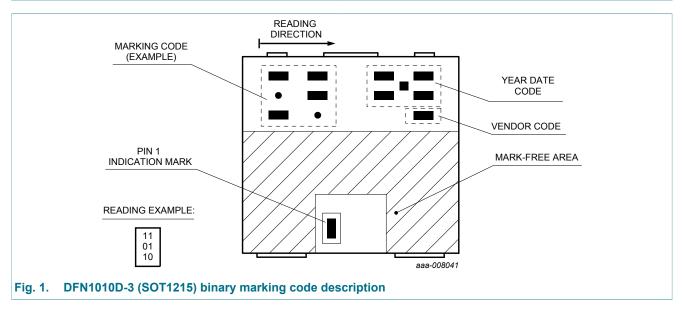
### 6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PBSS4160QA	DFN1010D-3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals	SOT1215			

### 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBSS4160QA	11 00 10



PBSS4160QA

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### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	60	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	60	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	7	V
I <sub>C</sub>	collector current			-	1	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	1.5	А
I <sub>B</sub>	base current			-	0.3	А
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	1	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	325	mW
			[2]	-	600	mW
			[3]	-	740	mW
			[4]	-	540	mW
			[5]	-	1000	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.

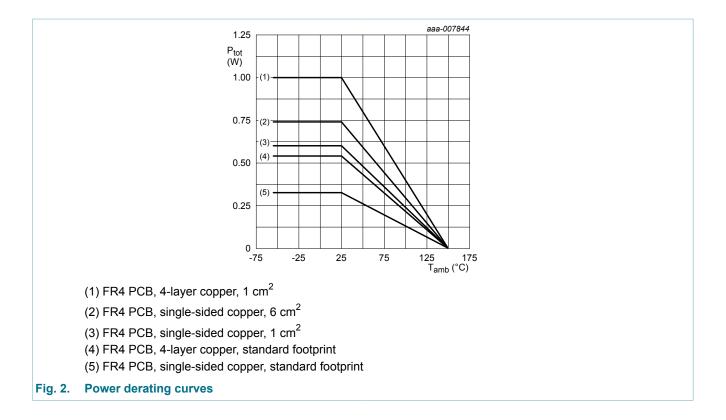
[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

<sup>[5]</sup> Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

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### 9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	in free air	[1]	-	-	385	K/W	
		[2]	-	-	209	K/W	
	ampient		[3]	-	-	169	K/W
			[4]	-	-	232	K/W
			[5]	-	-	125	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

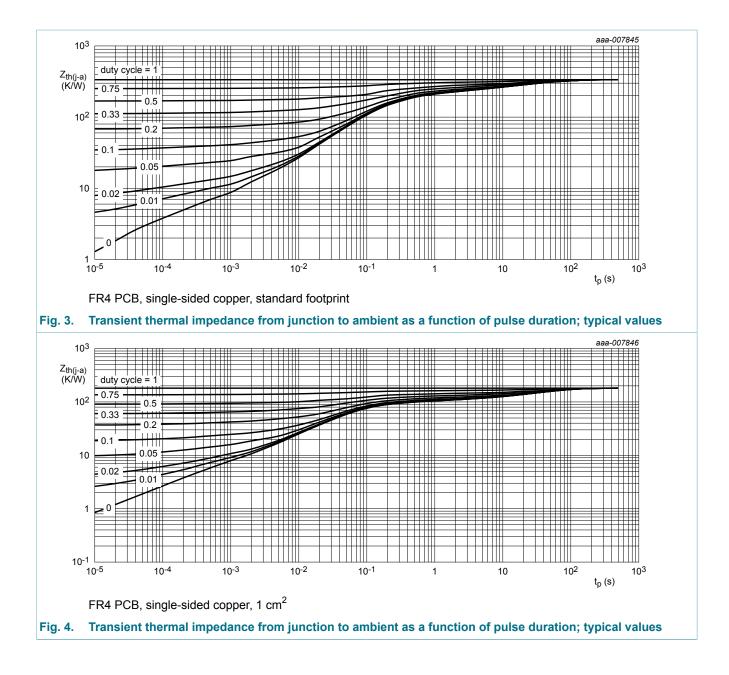
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

<sup>[5]</sup> Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

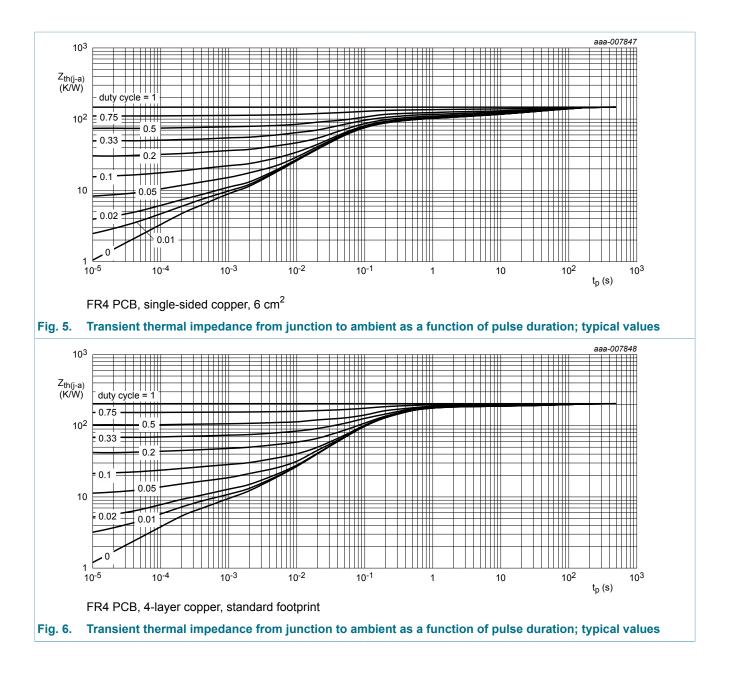


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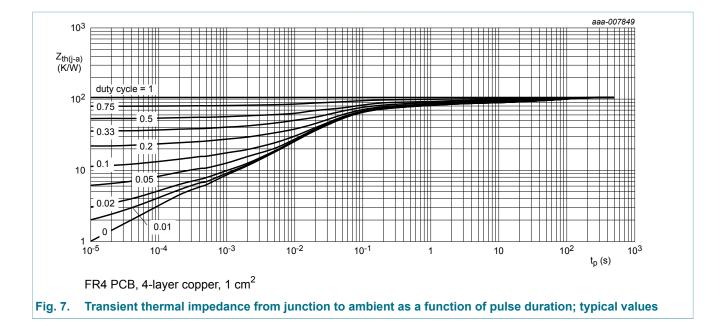
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### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 48 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 48 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 48 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 2 V; I <sub>C</sub> = 100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	230	400	-	
		$V_{CE}$ = 2 V; I <sub>C</sub> = 500 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	150	240	-	
		$\label{eq:Vce} \begin{split} V_{CE} &= 2 \; \text{V;} \; \text{I}_{C} = 1 \; \text{A; pulsed;} \; \text{t}_{p} \leq 300 \; \mu\text{s;} \\ \delta &\leq 0.02 \; \text{;} \; \text{T}_{amb} = 25 \; ^{\circ}\text{C} \end{split}$	85	130	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	-	90	125	mV
		$I_{C}$ = 1 A; $I_{B}$ = 50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	180	245	mV
		$I_{C}$ = 1 A; $I_{B}$ = 100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	170	235	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = 1 A; $I_{B}$ = 0.1 A; pulsed; $t_{p} \le 300 \ \mu$ s; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	170	235	mΩ

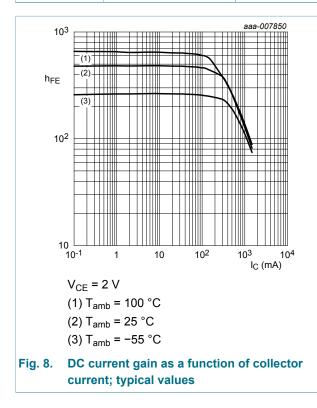
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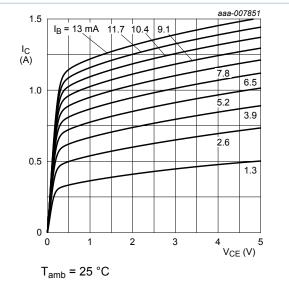
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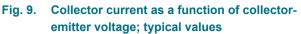
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>BEsat</sub> base-emitter saturation voltage	base-emitter saturation voltage	I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	-	0.89	1	V
		$I_{C}$ = 1 A; $I_{B}$ = 50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	0.94	1.05	V
	$I_{C}$ = 1 A; $I_{B}$ = 100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	0.98	1.1	V	
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE}$ = 2 V; I <sub>C</sub> = 0.5 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	-	0.78	0.9	V
t <sub>d</sub>	delay time	$V_{CC}$ = 10 V; I <sub>C</sub> = 0.5 A; I <sub>Bon</sub> = 25 mA; I <sub>Boff</sub> = -25 mA; T <sub>amb</sub> = 25 °C	-	15	-	ns
t <sub>r</sub>	rise time		-	85	-	ns
t <sub>on</sub>	turn-on time		-	100	-	ns
t <sub>s</sub>	storage time		-	545	-	ns
t <sub>f</sub>	fall time		-	125	-	ns
t <sub>off</sub>	turn-off time		-	670	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; I <sub>C</sub> = 50 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	120	180	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	4.7	6	pF



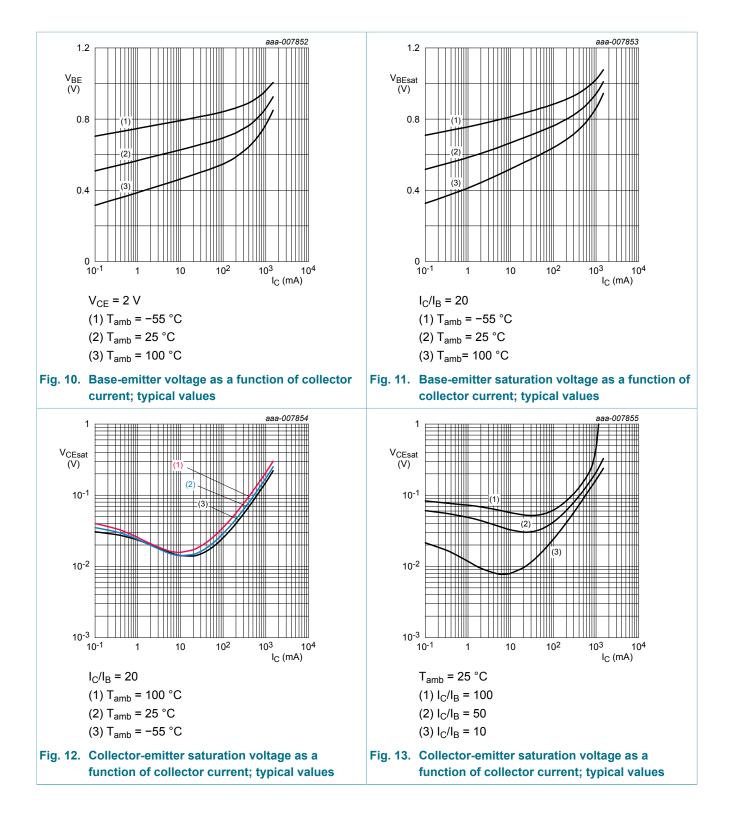




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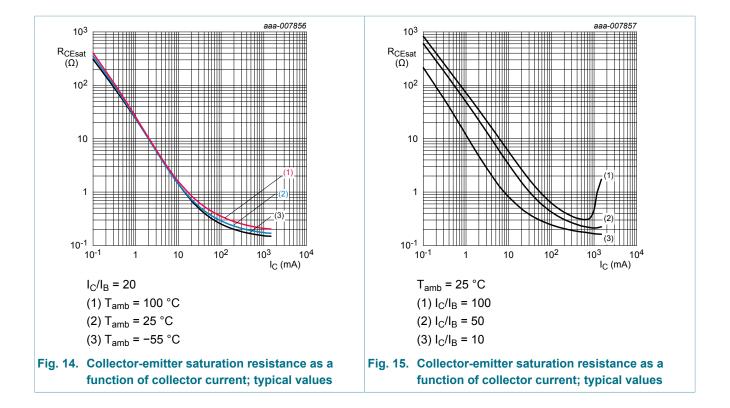
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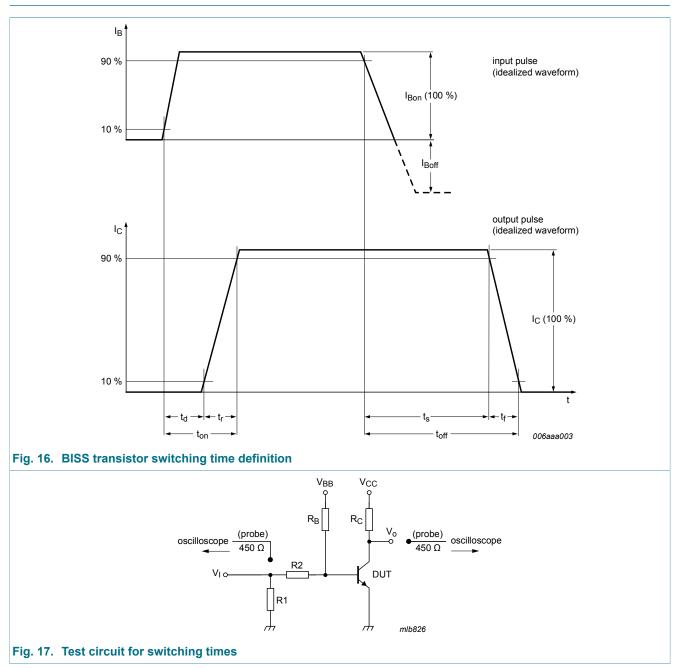
# PBSS4160QA

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### **11. Test information**

### **11.1 Quality information**

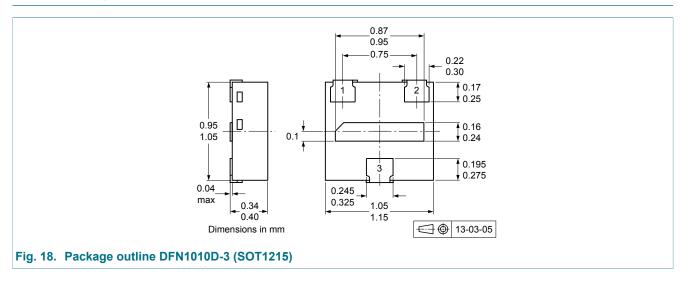
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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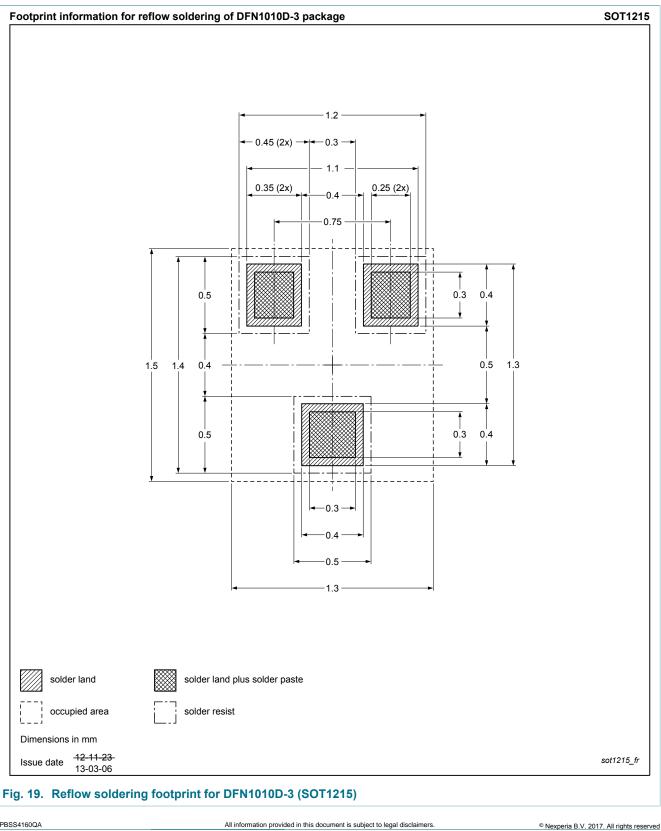
# 12. Package outline



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### 13. Soldering



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# 14. Revision history

Table 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PBSS4160QA v.1	20130823	Product data sheet	-	-	

#### 60 V, 1 A NPN low VCEsat (BISS) transistor

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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23 August 2013

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